NPN power transistor Rev. 1 — 29 July 2010

Preliminary data sheet

Product profile 1.

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) 3 leads plastic package.

1.2 Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability of 700 V

1.3 Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|--------------------------------|---|-----|------|-----|------|
| Ic | collector current | DC | - | - | 1.5 | Α |
| P _{tot} | total power dissipation | T _{lead} ≤ 25 °C; see <u>Figure 1</u> | - | i | 2.1 | W |
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0 V$ | | N.07 | 700 | V |
| Static cha | racteristics | | | | | |
| h _{FE} | DC current gain | $I_C = 0.5 \text{ A}; V_{CE} = 2 \text{ V};$ $T_{lead} = 25 ^{\circ}\text{C}$ | 8 | 17 | 25 | |





2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | В | base | | _ |
| 2 | С | collector | | C |
| 3 | E | E emitter | | BE sym123 |
| | | | SOT54 (TO-92) | |

3. Ordering information

Table 3. Ordering information

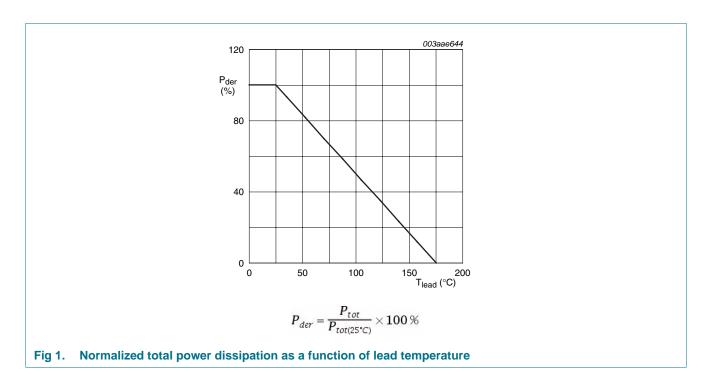
| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| PHE13003C | TO-92 | plastic single-ended leaded (through hole) package; 3 leads | SOT54 | | |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

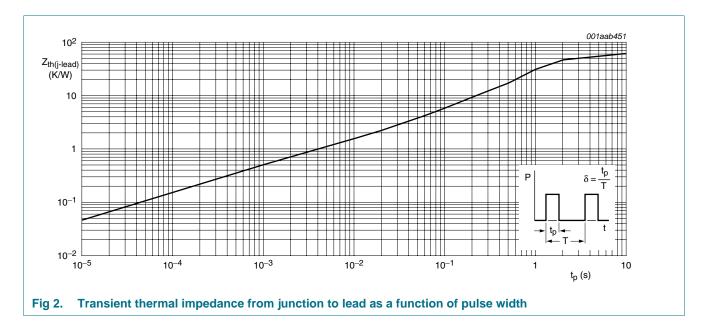
| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|--------------------------------|--|-----|------|------|
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0 V$ | - | 700 | V |
| V _{CBO} | collector-base voltage | I _E = 0 A | - | 700 | V |
| V _{CEO} | collector-emitter voltage | I _B = 0 A | - | 400 | V |
| I _C | collector current | DC | - | 1.5 | Α |
| I _{CM} | peak collector current | | - | 3 | Α |
| I _B | base current | DC | - | 0.75 | Α |
| I _{BM} | peak base current | | - | 1.5 | Α |
| P _{tot} | total power dissipation | T _{lead} ≤ 25 °C; see <u>Figure 1</u> | - | 2.1 | W |
| T _{stg} | storage temperature | | -65 | 150 | °C |
| Tj | junction temperature | | - | 150 | °C |
| V _{EBO} | emitter-base voltage | $I_C = 0 A$; $I(Emitter) = 10 mA$ | - | 9 | V |



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------|---|--|-----|-----|-----|------|
| $R_{\text{th(j-lead)}}$ | thermal resistance from junction to lead | see Figure 2 | - | - | 60 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air; printed-circuit board mounted; lead length = 4 mm | - | 150 | - | K/W |



PHE13003C

6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|---|-----|-----|-----|------|
| Static cha | racteristics | | | | | |
| I _{CES} | collector-emitter cut-off | $V_{BE} = 0 \text{ V}; V_{CE} = 700 \text{ V}; T_j = 125 ^{\circ}\text{C}$ | - | - | 5 | mA |
| | current | V _{BE} = 0 V; V _{CE} = 700 V; T _j = 25 °C | - | - | 1 | mΑ |
| I _{CEO} | collector-emitter cut-off current | V_{CE} = 400 V; I_{B} = 0 A; T_{lead} = 25 °C | - | - | 0.1 | mA |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$ | - | - | 1 | mA |
| V_{CEOsus} | collector-emitter sustaining voltage | $I_B = 0 \text{ A}$; $I_C = 1 \text{ mA}$; $L_C = 25 \text{ mH}$; $T_{lead} = 25 \text{ °C}$; see <u>Figure 3</u> ; see <u>Figure 4</u> | 400 | - | - | V |
| V _{CEsat} | collector-emitter | $I_C = 0.5 \text{ A}; I_B = 0.1 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$ | - | - | 0.5 | V |
| | saturation voltage | I _C = 1 A; I _B = 0.25 A; T _{lead} = 25 °C | - | - | 1 | V |
| | | I _C = 1.5 A; I _B = 0.5 A; T _{lead} = 25 °C | - | - | 1.5 | V |
| V _{BEsat} | base-emitter saturation | $I_C = 0.5 \text{ A}$; $I_B = 0.1 \text{ A}$; $T_{lead} = 25 ^{\circ}\text{C}$ | - | - | 1 | V |
| | voltage | I _C = 1 A; I _B = 0.25 A; T _{lead} = 25 °C | - | - | 1.2 | V |
| h _{FE} | DC current gain | $I_C = 0.5 \text{ A}$; $V_{CE} = 2 \text{ V}$; $T_{lead} = 25 ^{\circ}\text{C}$ | 8 | 17 | 25 | |
| | | I _C = 1 A; V _{CE} = 2 V; T _{lead} = 25 °C | 5 | 9 | 15 | |
| Dynamic (| characteristics | | | | | |
| t _{on} | turn-on time | $I_C = 1 \text{ A}$; $I_{Bon} = 0.2 \text{ A}$; $I_{Boff} = -0.2 \text{ A}$; | - | - | 1 | μs |
| t _s | storage time | R_L = 75 Ω; T_{lead} = 25 °C; resistive load; see <u>Figure 5</u> ; see <u>Figure 6</u> | - | - | 4 | μs |
| | | I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; see Figure 7; see Figure 8 | - | 8.0 | - | μs |
| t _f | fall time | I_C = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_L = 75 Ω ; T_{lead} = 25 °C; resistive load; see <u>Figure 5</u> ; see <u>Figure 6</u> | - | - | 0.7 | μs |
| | | $I_C = 0.5 \text{ A}$; $I_{Bon} = 0.1 \text{ A}$; $V_{BB} = -5 \text{ V}$; $L_B = 1 \mu H$; $T_{lead} = 25 \text{ °C}$; inductive load; see Figure 7; see Figure 8 | - | 0.1 | - | μs |

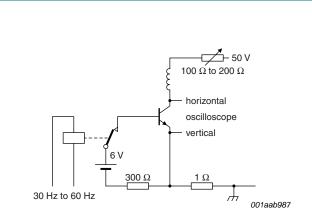


Fig 3. Test circuit for collector-emitter sustaining voltage

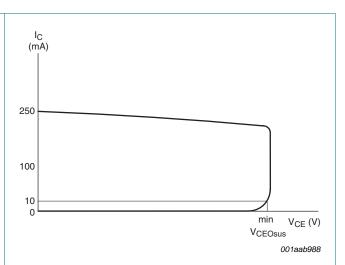
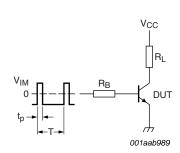


Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 $V_{IM}=-6$ to +8 V; $V_{CC}=250$ V; $t_p=20$ μs ; $\pmb{\delta}=\frac{t_p}{T}=0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

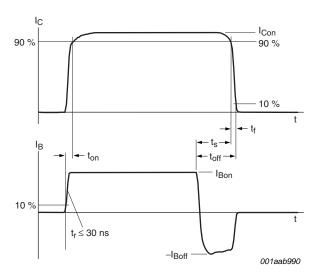
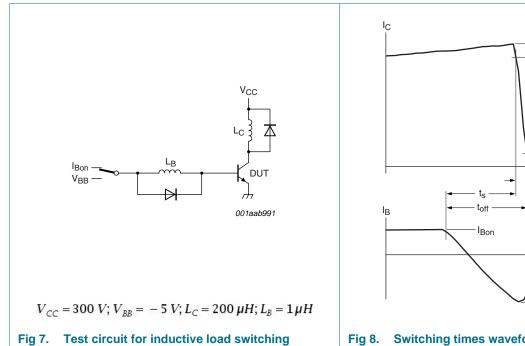
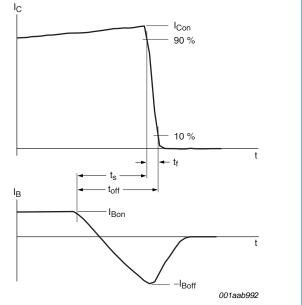


Fig 6. Switching times waveforms for resistive load



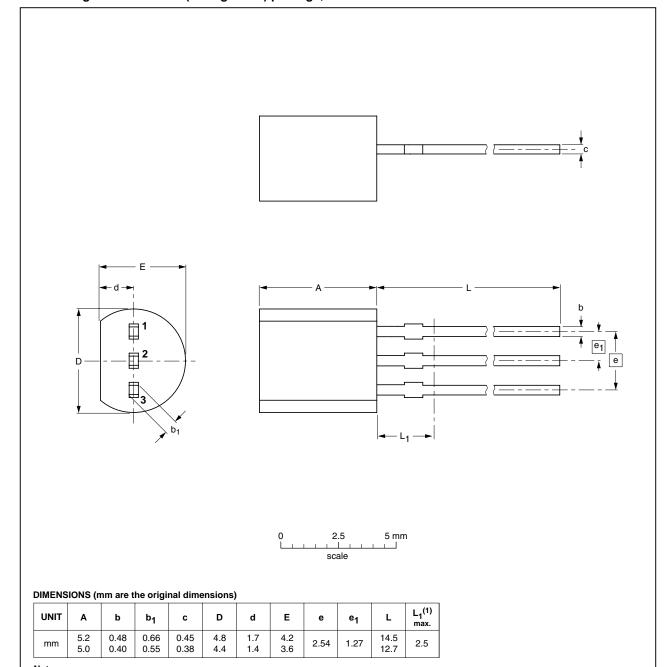


Switching times waveforms for inductive load Fig 8.

Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE VERSION | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|--------------------|-----|-------|--------|------------|-----------------------------------|
| | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT54 | | TO-92 | SC-43A | | -04-06-28 -04-11-16 |

Package outline SOT54 (TO-92)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|------------------------|---------------|------------|
| PHE13003C v.1 | 20100729 | Preliminary data sheet | - | - |

9. Legal information

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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NPN power transistor

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